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	PTO/SB/21 (08-00)	
Application Number	09/894,125	
Filing Date	June 29, 2001	
First Named Inventor	Shunpei YAMAZAKI et al.	
Group Art Unit	. 2823	
Examiner Name	B. Kebede	
Attorney Docket Number	0756-2330	

FORM (to be used for all correspondence after initial filing) Total Number of Pages in This Submission ENCLOSURES (check all that apply)

Fee Transmittal Form Fee Attached Amendment / Reply After Final Affidavits/declaration(s Extension of Time Request Express Abandonment Rec Information Disclosure Stat Certified Copy of Priority Document(s) Response to Missing Parts Incomplete Application Response to Missing P under 37 CFR 1.52 or	t quest tement	(for an Application) Drawing(s) Declaration and Power of Attorney Group Appeal Community Appeals and Appeal Community	charge any additional		
SIGNATURE OF APPLICANT, ATTORNEY, OR AGENT					
Firm or Individual name	Eric J. Robinson, Reg. No. 38,285 Robinson Intellectual Property Law Office, P.C.		EB 28 2003 -0GY CENTER 280		
Signature	5.	~	280		
Date	2-20	-03			
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Docket No. 0756-23

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Patent Application of Shunpei YAMAZAKI et al. Serial No. 09/894,125 < Filed: June 29, 2001 For: CRYSTALLINE SEMICONDUCTOR) THIN FILM, METHOD OF FABRICATING)

THE SAME, SEMICONDUCTOR DEVICE,)

AND METHOD OF FABRICATING THE

Examiner: B. Kebede **CERTIFICATE OF MAILING**

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Adele M. Stamper

Art Unit: 2823

AMENDMENT

Honorable Commissioner of Patents

Washington, D.C. 20231

Sir:

SAME

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able Commissioner of Patents

ngton, D.C. 20231

In response to the Official Action dated November 20, 2002, please articles and the province of Patents

| Commissioner of Patents | TECHNOLOGY | TECHN above-identified application as follows:

IN THE CLAIMS:

Please amend claims 1 and 7 as follows:

(Twice Amended) A method of manufacturing a semiconductor device 1. comprising the steps of:

forming a semiconductor film comprising silicon over a substrate;

irradiating said semiconductor film with laser light in air for crystallizing said semiconductor film;

removing a natural oxidation film formed on a surface of the semiconductor film by etching after the irradiation of the laser light; and

leveling the surface of the semiconductor film by heating after removing said natural oxidation film.